NL17SG32

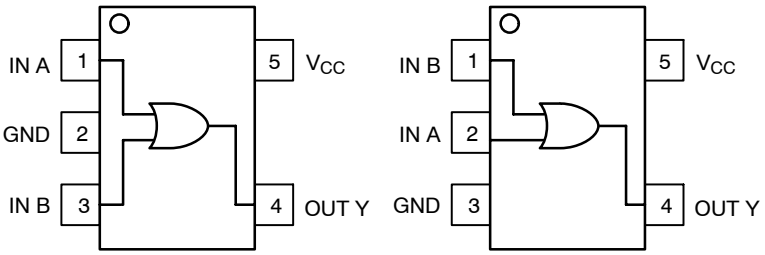
Single 2-Input OR Gate

The NL17SG32 MiniGate™ is an advanced high−speed CMOS 2−input OR gate in ultra−small footprint.

The NL17SG32 input structures provides protection when voltages up to 4.6 V are applied.

Features

- Wide Operating V_{CC} Range: 0.9 V to 3.6 V
- High Speed: t_{PD} = 2.4 ns (Typ) at V_{CC} = 3.0 V, C_L = 15 pF
- Low Power Dissipation: I_{CC} = 0.5 μA (Max) at T_A = 25°C
- 4.6 V Overvoltage Tolerant (OVT) Input Pins
- Ultra−Small Packages
- These are Pb−Free and Halide−Free Devices



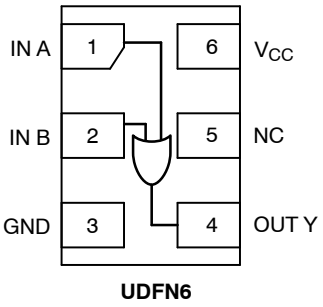


Figure 1. Pinouts (Top View)

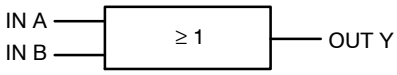
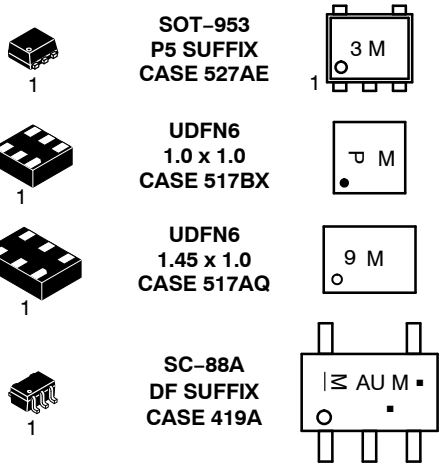


Figure 2. Logic Symbol

ON Semiconductor®

www.onsemi.com

MARKING DIAGRAMS



M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

PIN ASSIGNMENT

	SOT−953	SC−88A	UDFN6
1	IN A	IN B	IN A
2	GND	IN A	IN B
3	IN B	GND	GND
4	OUT Y	OUT Y	OUT Y
5	V_{CC}	V_{CC}	NC
6			V_{CC}

FUNCTION TABLE

A Input	B Input	Y Output
L	L	L
L	H	H
H	L	H
H	H	H

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V_{CC}	DC Supply Voltage		−0.5 to +5.5	V
V_{IN}	DC Input Voltage		−0.5 to +4.6	V
V_{OUT}	DC Output Voltage	Output at High or Low State Power−Down Mode (V_{CC} = 0 V)	−0.5 to V_{CC} +0.5 −0.5 to +4.6	V
I_{IK}	DC Input Diode Current	V_{IN} < GND	−20	mA
I_{OK}	DC Output Diode Current	V_{OUT} < GND	−20	mA
I_{OUT}	DC Output Source/Sink Current		±20	mA
I_{CC}	DC Supply Current per Supply Pin		±20	mA
I_{GND}	DC Ground Current per Ground Pin		±20	mA
T_{STG}	Storage Temperature Range		−65 to +150	°C
T_L	Lead Temperature, 1 mm from Case for 10 Seconds		260	°C
T_J	Junction Temperature Under Bias		+150	°C
MSL	Moisture Sensitivity		Level 1	
F_R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V−0 @ 0.125 in	
V_{ESD}	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3)	>2000 >200	V
$I_{LATCHUP}$	Latchup Performance	Above V_{CC} and Below GND at 125°C (Note 4)	±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Measured with minimum pad spacing on an FR4 board, using 10 mm−by−1 inch, 2−ounce copper trace with no air flow.
2. Tested to EIA/JESD22−A114−A.
3. Tested to EIA/JESD22−A115−A.
4. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics		Min	Max	Unit
V_{CC}	Positive DC Supply Voltage		0.9	3.6	V
V_{IN}	Digital Input Voltage		0.0	3.6	V
V_{OUT}	Output Voltage	Output at High or Low State Power−Down Mode (V_{CC} = 0 V)	0.0 0.0	V_{CC} 3.6	V
T_A	Operating Temperature Range		−55	+125	°C
$\Delta t / \Delta V$	Input Transition Rise or Fail Rate	V_{CC} = 3.3 V ± 0.3 V	0	10	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Conditions		V_{CC} (V)	T_A = 25°C		T_A = -55°C to +125°C		Unit
					Min	Max	Min	Max	
V_{IH}	High-Level Input Voltage			0.9	V_{CC}		V_{CC}		V
				1.1 to 1.3	0.7xV_{CC}		0.7xV_{CC}		
				1.4 to 1.6	0.65xV_{CC}		0.65xV_{CC}		
				1.65 to 1.95	0.65xV_{CC}		0.65xV_{CC}		
				2.3 to 2.7	1.7		1.7		
				3.0 to 3.6	2.0		2.0		
V_{IL}	Low-Level Input Voltage			0.9		GND		GND	V
				1.1 to 1.3		0.3xV_{CC}		0.3xV_{CC}	
				1.4 to 1.6		0.35xV_{CC}		0.35xV_{CC}	
				1.65 to 1.95		0.35xV_{CC}		0.35xV_{CC}	
				2.3 to 2.7		0.7		0.7	
				3.0 to 3.6		0.8		0.8	
V_{OH}	High-Level Output Voltage	V_{IN} = V_{IH} or V_{IL}	I_{OH} = −20 μA	0.9	0.75		0.75		V
			I_{OH} = -0.3 mA	1.1 to 1.3	0.75xV_{CC}		0.75xV_{CC}		
			I_{OH} = -1.7 mA	1.4 to 1.6	0.75xV_{CC}		0.75xV_{CC}		
			I_{OH} = -3.0 mA	1.65 to 1.95	Vcc-0.45		Vcc-0.45		
			I_{OH} = -4.0 mA	2.3 to 2.7	2.0		2.0		
			I_{OH} = -8.0 mA	3.0 to 3.6	2.48		2.48		
V_{OL}	Low-Level Output Voltage	V_{IN} = V_{IH} or V_{IL}	I_{OL} = 20 μA	0.9 to 3.6		0.1		0.1	V
			I_{OL} = 1.1 mA	1.1 to 1.3		0.25xV_{CC}		0.25xV_{CC}	
			I_{OL} = 1.7 mA	1.4 to 1.6		0.25xV_{CC}		0.25xV_{CC}	
			I_{OL} = 3.0 mA	1.65 to 1.95		0.45		0.45	
			I_{OL} = 4.0 mA	2.3 to 2.7		0.4		0.4	
			I_{OL} = 8.0 mA	3.0 to 3.6		0.4		0.4	
I_{IN}	Input Leakage Current	0 ≤ V_{IN} ≤ 3.6 V		0 to 3.6		±0.1		±1.0	μA
I_{CC}	Quiescent Supply Current	V_{IN} = V_{CC} or GND		3.6		0.5		10.0	μA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0$ ns)

Symbol	Parameter	Test Condition	V_{CC} (V)	T_A = 25° C			T_A = -55°C to +125°C		Unit
				Min	Typ	Max	Min	Max	
t_{PLH}, t_{PHL}	Propagation Delay, A or B to Y	C_L = 10 pF, R_L = 1 MΩ	0.9	-	12.2	14.4	-	18.0	ns
			1.1 to 1.3	-	8.8	12.4	-	16.2	
			1.4 to 1.6	-	5.0	8.5	-	10.0	
			1.65 to 1.95	-	3.6	6.2	-	6.7	
			2.3 to 2.7	-	2.7	3.9	-	4.4	
			3.0 to 3.6	-	2.1	3.1	-	3.7	
		C_L = 15 pF, R_L = 1 MΩ	0.9	-	13.0	16.0	-	18.0	ns
			1.1 to 1.3	-	7.8	12.0	-	16.0	
			1.4 to 1.6	-	5.9	9.3	-	11.2	
			1.65 to 1.95	-	4.5	6.9	-	7.1	
			2.3 to 2.7	-	3.0	4.4	-	5.0	
			3.0 to 3.6	-	2.4	3.4	-	3.9	
		C_L = 30 pF, R_L = 1 MΩ	0.9	-	14.0	17.2	-	20.0	ns
			1.1 to 1.3	-	11.0	14.1	-	17.8	
			1.4 to 1.6	-	8.0	12.1	-	15.9	
			1.65 to 1.95	-	6.0	9.2	-	9.6	
			2.3 to 2.7	-	3.9	5.7	-	6.1	
			3.0 to 3.6	-	3.0	4.4	-	4.8	
C_{IN}	Input Capacitance		0 to 3.6		3	-	-	-	pF
C_{PD}	Power Dissipation Capacitance (Note 5)	f = 10 MHz	0.9 to 3.6	-	4	-	-	-	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$. C_{PD} is used to determine the no−load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.

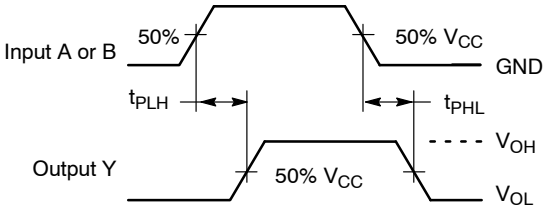
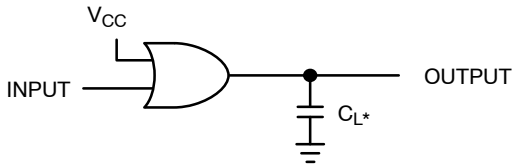


Figure 3. Switching Waveforms



*Includes all probe and jig capacitance.
A 1−MHz square input wave is recommended
for propagation delay tests.

Figure 4. Test Circuit

ORDERING INFORMATION

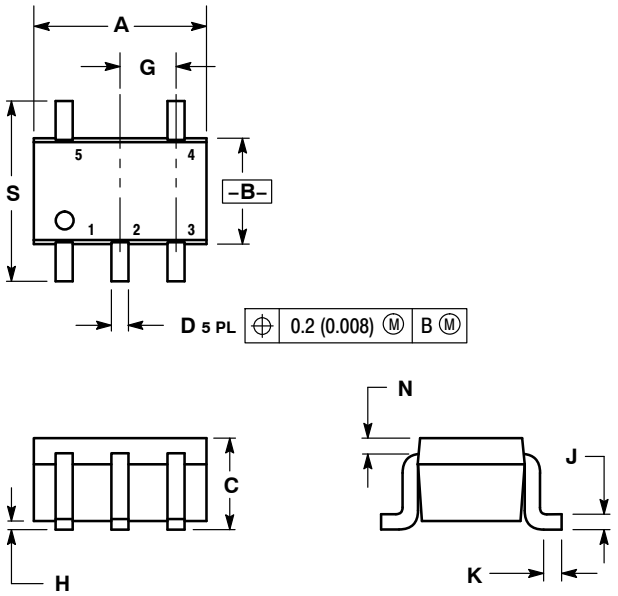
Device	Package	Shipping†
NL17SG32P5T5G	SOT−953 (Pb−Free)	8000 / Tape & Reel
NL17SG32DFT2G	SC−88A (Pb−Free)	3000 / Tape & Reel
NL17SG32AMUTCG	UDFN6 1.45 x 1 mm (Pb−Free)	3000 / Tape & Reel
NL17SG32CMUTCG	UDFN6 1 x 1 mm (Pb−Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

SC−88A (SC−70−5/SOT−353)
CASE 419A−02
ISSUE L

SCALE 2:1

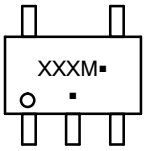
DATE 17 JAN 2013



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 419A−01 OBSOLETE. NEW STANDARD 419A−02.
4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026 BSC		0.65 BSC	
H	---	0.004	---	0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.012	0.10	0.30
N	0.008 REF		0.20 REF	
S	0.079	0.087	2.00	2.20

GENERIC MARKING DIAGRAM*

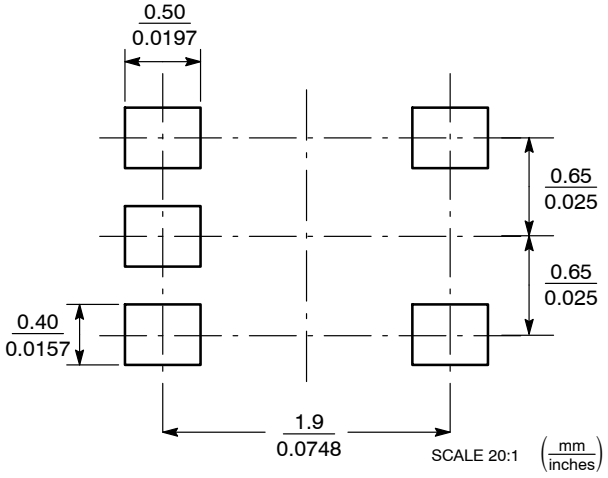


XXX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*This infomration is generic. Please refer to device data sheet for actual part marking.

SOLDER FOOTPRINT



STYLE 1:
PIN 1. BASE
2. EMITTER
3. BASE
4. COLLECTOR
5. COLLECTOR

STYLE 2:
PIN 1. ANODE
2. EMITTER
3. BASE
4. COLLECTOR
5. CATHODE

STYLE 3:
PIN 1. ANODE 1
2. N/C
3. ANODE 2
4. CATHODE 2
5. CATHODE 1

STYLE 4:
PIN 1. SOURCE 1
2. DRAIN 1/2
3. SOURCE 1
4. GATE 1
5. GATE 2

STYLE 5:
PIN 1. CATHODE
2. COMMON ANODE
3. CATHODE 2
4. CATHODE 3
5. CATHODE 4

STYLE 6:
PIN 1. EMITTER 2
2. BASE 2
3. EMITTER 1
4. COLLECTOR
5. COLLECTOR 2/BASE 1

STYLE 7:
PIN 1. BASE
2. EMITTER
3. BASE
4. COLLECTOR
5. COLLECTOR

STYLE 8:
PIN 1. CATHODE
2. COLLECTOR
3. N/C
4. BASE
5. EMITTER

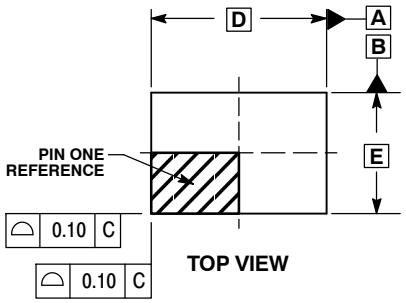
STYLE 9:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. ANODE
5. ANODE

ISSUE	REVISION	DATE
C	CONVERTED FROM PAPER DOCUMENT TO ELECTRONIC. REQ. BY N LAFEBRE.	20 JUN 1998
D	CONVERTED FROM MOTOROLA TO ON SEMICONDUCTOR. ADDED STYLE 5. REQ. BY E. KIM.	24 JUL 2000
E	ADDED STYLES 6 & 7. REQ. BY S. BACHMAN.	03 AUG 2000
F	DELETED DIMENSION V, WAS 0.3−0.44MM/0.012−0.016IN. REQ. BY G. KWONG.	14 JUN 2001
G	ADDED STYLE 8, REQ. BY S. CHANG; ADDED STYLE 9, REQ. BY S. BACHMAN; ADDED NOTE 4, REQ. BY S. RIGGS	25 JUN 2003
H	CHANGED STYLE 6. REQ. BY C. LIM	28 APR 2005
J	CHANGED TITLE DESCRIPTION. REQ. BY B. LOFTS.	31 AUG 2005
K	CORRECTED TITLE AND DESCRIPTION TO SC−88A (SC−70−5/SOT−353). CORRECTED MARKING DIAGRAM. REQ. BY D. TRUHITTE.	13 JUL 2010
L	ADDED SOLDER FOOTPRINT. REQ. BY I. MARIANO.	17 JAN 2013

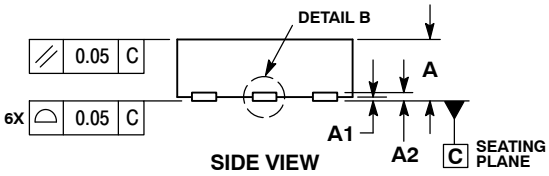
UDFN6, 1.45x1.0, 0.5P
CASE 517AQ−01
ISSUE O

DATE 15 MAY 2008

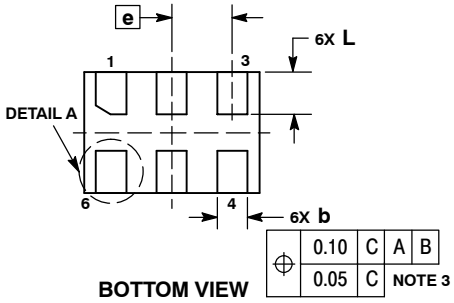
SCALE 4:1



TOP VIEW

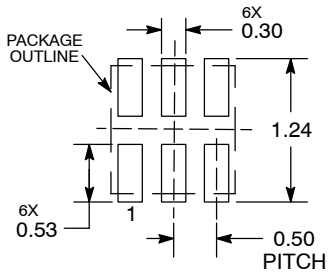


SIDE VIEW



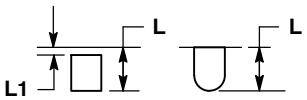
BOTTOM VIEW

MOUNTING FOOTPRINT

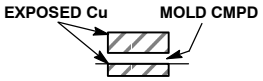


DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



DETAIL A
OPTIONAL CONSTRUCTIONS



DETAIL B
OPTIONAL CONSTRUCTIONS

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 mm FROM THE TERMINAL TIP.

	MILLIMETERS	
DIM	MIN	MAX
A	0.45	0.55
A1	0.00	0.05
A2	0.07 REF	
b	0.20	0.30
D	1.45 BSC	
E	1.00 BSC	
e	0.50 BSC	
L	0.30	0.40
L1	−−−	0.15

GENERIC MARKING DIAGRAM*

X = Specific Device Code
M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present.

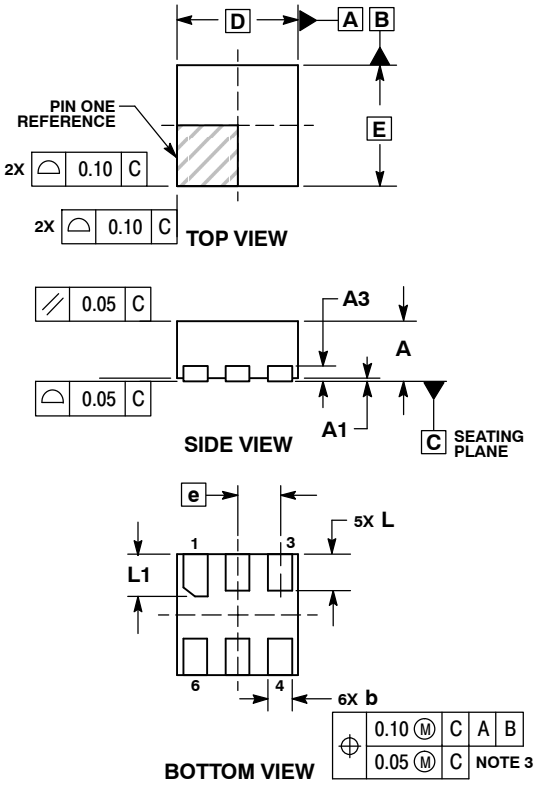
DOCUMENT NUMBER:	**98AON30313E**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.	
STATUS:	**ON SEMICONDUCTOR STANDARD**		
NEW STANDARD:			
DESCRIPTION:	**UDFN6, 1.45X1.0, 0.5P**		**PAGE 1 OF 2**

ISSUE	REVISION	DATE
O	RELEASED FOR PRODUCTION. REQ. BY K. VAN TYNE.	15 MAY 2008

UDFN6, 1x1, 0.35P
CASE 517BX−01
ISSUE O

SCALE 4:1

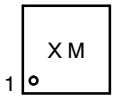
DATE 18 MAY 2011



NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.20 MM FROM TERMINAL TIP.
4. PACKAGE DIMENSIONS EXCLUSIVE OF BURRS AND MOLD FLASH.

	MILLIMETERS	
DIM	MIN	MAX
A	0.45	0.55
A1	0.00	0.05
A3	0.13 REF	
b	0.12	0.22
D	1.00 BSC	
E	1.00 BSC	
e	0.35 BSC	
L	0.25	0.35
L1	0.30	0.40

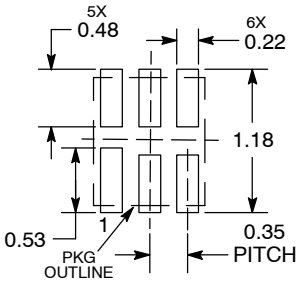
GENERIC MARKING DIAGRAM*



X = Specific Device Code
M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present.

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ISSUE	REVISION	DATE
O	RELEASED FOR PRODUCTION. REQ. BY I. CAMBALIZA.	18 MAY 2011

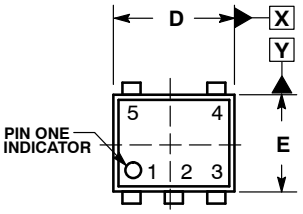
MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

ON Semiconductor®

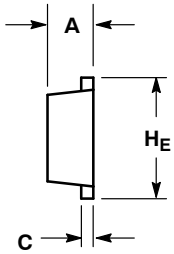
SOT−953
CASE 527AE
ISSUE E

DATE 02 AUG 2011

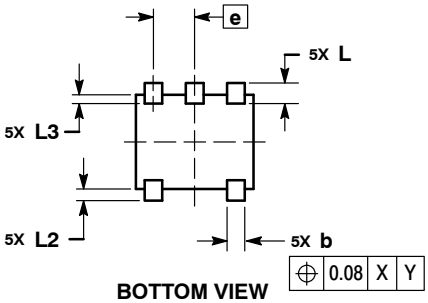
SCALE 4:1



TOP VIEW



SIDE VIEW

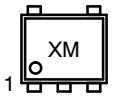


BOTTOM VIEW

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS		
DIM	MIN	NOM	MAX
A	0.34	0.37	0.40
b	0.10	0.15	0.20
C	0.07	0.12	0.17
D	0.95	1.00	1.05
E	0.75	0.80	0.85
e	0.35 BSC		
H_E	0.95	1.00	1.05
L	0.175 REF		
L2	0.05	0.10	0.15
L3	−−−	−−−	0.15

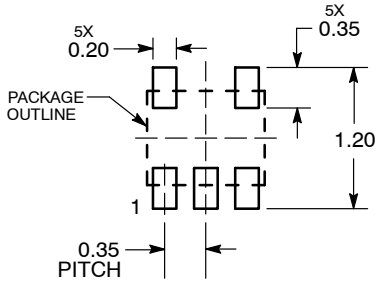
GENERIC MARKING DIAGRAM*



X = Specific Device Code
M = Month Code

*This information is generic. Please refer to device data sheet for actual part marking.
Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present.

SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DOCUMENT NUMBER:	**98AON26457D**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.
DESCRIPTION:	**SOT−953**	**PAGE 1 OF 1**

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Email Requests to: orderlit@onsemi.com

ON Semiconductor Website: www.onsemi.com

TECHNICAL SUPPORT
North American Technical Support:
Voice Mail: 1 800−282−9855 Toll Free USA/Canada
Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:
Phone: 00421 33 790 2910
For additional information, please contact your local Sales Representative

◊